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# Is There a Unified Description of Conductivity of Layered Cuprates ?[1]

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*We present a novel approach to the analysis of the normal state in-plane $\sigma_{ab}$ and out-of-plane $\sigma_c$ conductivities of anisotropic layered crystals such as oxygen deficient $YBa_2Cu_3O_x$. It can be shown that the resistive anisotropy is determined by the ratio of the phase coherence lengths in the respective directions; i.e., $\sigma_{ab}/\sigma_c = \ell_{ab}^2/\ell_c^2$. From the idea that at all doping levels and temperatures $T$ the out-of-plane transport in these crystals is incoherent, follows that $\ell_c$ is $T$-independent, equal to the spacing $\ell_0$ between the neighboring bilayers. Thus, the $T$-dependence of $\ell_{ab}$ is given by the measured anisotropy, and $\sigma_{ab}(\ell_{ab})$ dependence is obtained by plotting $\sigma_{ab}$ vs $\ell = (\sigma_{ab}/\sigma_c)^{1/2}\ell_0$. The analysis of several single crystals of $YBa_2Cu_3O_x$ ($6.35 < x < 6.93$) shows that for all of them $\sigma_{ab}(\ell)$ is described by a universal dependence $\sigma_{ab}/\bar{\sigma} = f(\ell/\bar{\ell})$ with doping dependent parameters $\bar{\sigma}$ and $\bar{\ell}$.*

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The temperature $T$ dependence of the in-plane $\rho_{ab}$ and out-of-plane $\rho_c$ normal state resistivities of layered cuprates such as $YBa_2Cu_3O_{7-\delta}$ shows a diverse behavior ranging from metallic in optimally-doped and overdoped samples, to the coexistence of metallic $\rho_{ab}$ and nonmetallic $\rho_c$ in moderately underdoped crystals, to insulating $\rho_{ab}$ and $\rho_c$ in strongly underdoped specimens. A common feature of all cuprates is a very large ($\sim 10^2 - 10^5$) and temperature dependent anisotropy $\rho_c/\rho_{ab}$. Quasiclassical estimates of the mean free path in the c-direction indicate that it is less than the interlayer spacing even in the least anisotropic systems such as optimally-

doped $YBa_2Cu_3O_{7-\delta}$.[2] This means that the normal-state transport in the c-direction is incoherent at all temperatures so that the wave function of the electrons loses its coherence over the shortest possible distance, the interlayer spacing $\ell_0$, while the coherence length [hereafter called Thouless length (TL)] in the $CuO_2$ planes is much larger than the size of the unit cell, as evidenced by the values of $\rho_{ab}$ which are well below the Mott's limit.[2]

The layered crystals with incoherent interlayer transitions represent a unique system in which the strong interlayer decoherence of the charge carrier's wave function could be the reason for the strong $T$ dependence of the resistive anisotropy. This follows from the general relationship between conductivities:[3]

$$\frac{\sigma_{ab}}{\sigma_c} = \frac{\ell^2}{\ell_c^2}. \tag{1}$$

Here $\ell$ is the in-plane TL and $\ell_c$ is the out-of-plane TL. In conventional metals, the two phase coherence lengths change with temperature at the same rate so that $\sigma_{ab}/\sigma_c = const.$ The strong interlayer decoherence in layered crystals (of still unknown origin) implies that $\ell_c$ is temperature independent, equal to the interlayer spacing; i.e., $\ell_c = \ell_0$. As a result, the anisotropy is temperature dependent, reflecting the $T$ dependence of the in-plane phase coherence length. Thus, the layered crystals with incoherent interlayer transitions offer the opportunity to obtain experimentally both the in-plane TL (by measuring $\rho_c/\rho_{ab}$) and the functional dependence of $\sigma_{ab}$ on the phase coherence length [by plotting $\sigma_{ab}$ vs $(\rho_c/\rho_{ab})^{1/2}\ell_0$].

We performed measurements of both $\rho_{ab}$ and $\rho_c$ as a function of T ($T_c < T \leq 300\ K$) on $YBa_2Cu_3O_x$ ($6.35 \leq x \leq 6.93$) single crystals using the four-point method, as well as the multiterminal technique (flux-transformer geometry[4]). Figure 1 is a plot of $\sigma_{ab}$ vs $\ell = (\rho_c/\rho_{ab})^{1/2}\ell_0$ with $\ell_0 = 11.7\mathring{A}$. The open symbols represent the raw data. An idea outlined in Ref. 3 is that the variation with doping of the number of carriers and the amount of disorder does not alter fundamentally the $\sigma(\ell)$ dependence, and that the effect of these changes can be incorporated into two constants, one of which, $\bar{\sigma}$, normalizes the magnitude of the in-plane conductivity, and the other, $\bar{\ell}$, normalizes the in-plane Thouless length, namely,

$$\frac{\sigma_{ab}}{\bar{\sigma}} = f\left(\frac{\ell}{\bar{\ell}}\right); \quad f(1) = 1. \tag{2}$$

Here $f(y)$ is the same function for a given class of single crystals, such as $YBa_2Cu_3O_x$. Varying oxygen content in this case only changes the values of the normalization constants $\bar{\sigma}$ and $\bar{\ell}$, shifting the respective segments of $\sigma_{ab}(\ell)$ along a common trajectory.

The continuous curve indicated in Fig. 1 by the filled symbols is generated by shifting the segments corresponding to different oxygen concen-

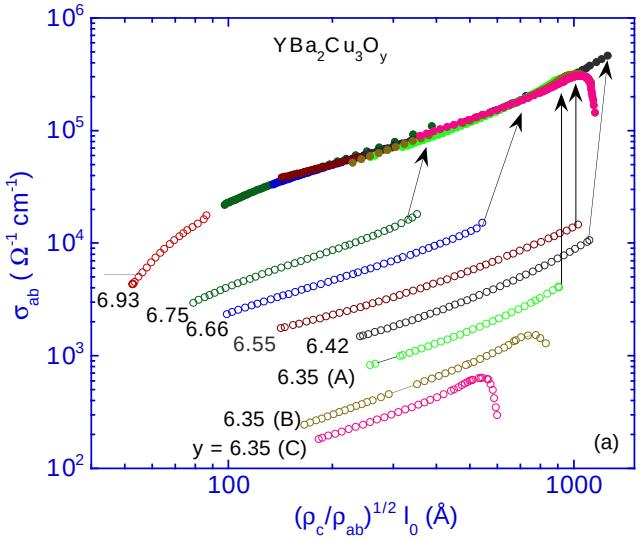


Fig. 1. *In-plane conductivity $\sigma_{ab}$ of $YBa_2Cu_3O_x$ single crystals plotted vs phase coherence length defined as $\ell = (\rho_c/\rho_{ab})^{1/2}\ell_0$, with $\ell_0 = 11.7\AA$. The open symbols correspond to the raw data. For all samples the lowest anisotropy corresponds to highest temperature and vice versa. The filled symbols which form a trajectory [Eq. (2)] are obtained by shifting the open symbol segments parallel to themselves as indicated by the arrows.*

trations parallel to themselves (as indicated by the arrows), matching the values and the slopes of the *overlapping* segments. The data for the $x = 6.93$ sample were used as reference. On a log-log plot, such shifts are equivalent to change of normalization constants $\bar{\sigma}$ and $\bar{\ell}$. Through this procedure we obtained the trajectory $\sigma_{ab}(\ell)$ given by Eq. (2), with the values of $\bar{\sigma}$ and $\bar{\ell}$ corresponding to the oxygen content of the reference sample ($x = 6.93$). The branching point reflects the metal-insulator transition.

Here we consider in more detail the functional dependence $\sigma_{ab}(\ell)$ of the optimally doped $YBa_2Cu_3O_{6.93}$ single crystal. Figure 2(a) shows its conductivity plotted vs $\ell$. This $\sigma_{ab}(\ell)$ dependence is well described by:

$$\sigma_{ab} = q(\ell - \xi); \quad \ell > \xi. \tag{3}$$

Based on Eq. (1), the corresponding $\sigma_c$ is given by

$$\sigma_c = q\ell_0^2\left(\frac{1}{\ell} - \frac{\xi}{\ell^2}\right). \tag{4}$$

Note that $\sigma_c$ is metallic ($d\sigma_c/d\ell > 0$) for $\ell < 2\xi$, and nonmetallic ($d\sigma_c/d\ell < 0$) for $\ell > 2\xi$. Since the phase coherence length monotonically increases with decreasing temperature, $\sigma_c$ is metallic at high $T$, reaches a maximum

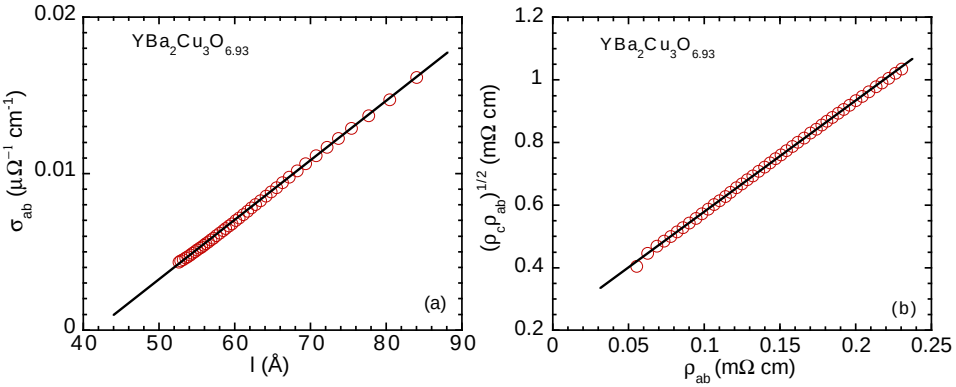


Fig. 2. *(a) In-plane conductivity of* $YBa_2Cu_3O_{6.93}$ *crystal plotted vs phase coherence length* $\ell$*; (b) same data plotted as* $(\rho_c\rho_{ab})^{1/2}$ *vs* $\rho_{ab}$ *[see Eq. (5)].*

when $\ell(T) = 2\xi$, and decreases with further decreasing $T$, while $\sigma_{ab}$ remains metallic at all $T$. Equations (3) and (4) are equivalent to the following relationship between resistivities:

$$(\rho_c\rho_{ab})^{1/2} = \bar{\rho} + \left(\frac{\xi}{\ell_0}\right)\rho_{ab}; \quad \bar{\rho} = \frac{1}{q\ell_0}. \tag{5}$$

Figure 2(b) is a plot of $(\rho_c\rho_{ab})^{1/2}$ vs $\rho_{ab}$. A fit of the data with Eq. (5) gives $\bar{\rho} \approx 0.23\ m\Omega\ cm$ and $\xi \approx 41\ \mathring{A}$. Thus, the temperature dependence of $\rho_c$ is determined by that of $\rho_{ab}$:

$$\rho_c = \left(\frac{\xi}{\ell_0}\right)^2 \rho_{ab} + 2\left(\frac{\xi}{\ell_0}\right)\bar{\rho} + \frac{\bar{\rho}^2}{\rho_{ab}}. \tag{6}$$

Specifically, when $\rho_{ab} = \alpha_{ab}T$, which is characteristic of the optimally doped $YBa_2Cu_3O_{7-\delta}$,

$$\rho_c = \beta_c + \alpha_c T + \frac{\gamma_c}{T}. \tag{7}$$

Note, that the minimum in $\rho_c$ for our sample is barely reached at the lowest temperature near $T_c$ (see Fig. 2a, where the maximum of $\ell \approx 82\mathring{A} \approx 2\xi$ ).

The origin of Eq. (3) can be understood from the conventional quasi-classical description of the in-plane conductivity:

$$\sigma_{ab} = \frac{e^2 n\tau}{m}, \tag{8}$$

where $\tau$ is the relaxation time of the distribution function. The phase coherence length can be expressed as

$$\ell = v_F\tau_\varphi + \xi, \tag{9}$$

where $\tau_\varphi$ is the decoherence time and $v_F$ is the Fermi velocity. We introduced the empirical cutoff $\xi$ to indicate that the phase coherence length in a crystal does not scale to zero with decreasing $\tau_\varphi$. The value of $\xi$ should correlate with elastic mean free path, because elastic collisions do not cause loss of phase coherence. Equation (9) reflects the ballistic (not diffusive) nature of the motion between the phase relaxation events. If we assume that the decoherence time and the relaxation time of the distribution function are proportional to each other, i.e. $\tau_\varphi = A\tau$ ($A = const$), Eq. (3) follows with $q = e^2 n/mv_F A$.

If, instead of Eq. (9), $\ell$ is determined by diffusion, i.e., $\ell^2 = D\tau_\varphi + \xi^2$, then, instead of Eq. (5), there is the following linear correlation between $\rho_c$ and $\rho_{ab}$: $\rho_c = \beta_c + (\xi^2/\ell_0^2)\rho_{ab}$. We find, however, that the ballistic motion of the electrons between phase relaxation collisions, namely Eqs. (3) and (9), describes appreciably better the resistivity data of $YBa_2Cu_3O_{6.93}$.

In summary, we have analyzed the resistivity data of $YBa_2Cu_3O_x$ ($6.35 < x < 6.93$) assuming that the interlayer phase coherence length is temperature independent, equal to the spacing between the neighboring bilayers. Under this condition, the out-of-plane transport is non-classical and $\sigma_c$ cannot be obtained from Boltzmann-Landau kinetic equation. Instead, we use the relationship between conductivities given by Eq. (1). Then, the out-of-plane conductivity is determined by the relationship between the in-plane phase coherence length and the relaxation time $\tau$. This relationship may be different for different systems. We also found that $\sigma_{ab}$ of single crystals with different oxygen content can be well described by a universal two parameter dependence on the in-plane TL which exhibits a branching point corresponding to the metal-insulator transition.

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